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(12) **United States Design Patent**
Asaka et al.

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(54) **SEMICONDUCTOR MEMORY ELEMENT**

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(**) **Term:** **14 Years**

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(30) **Foreign Application Priority Data**

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(51) **LOC (7) Cl.** **13-03**

(52) **U.S. Cl.** **D13/182; D14/435**

(58) **Field of Search** D14/432, 433, D14/434, 435, 436, 437, 438; D13/182; 174/52.2; 257/659, 666, 668, 687, 704, 787; 361/212, 816, 820

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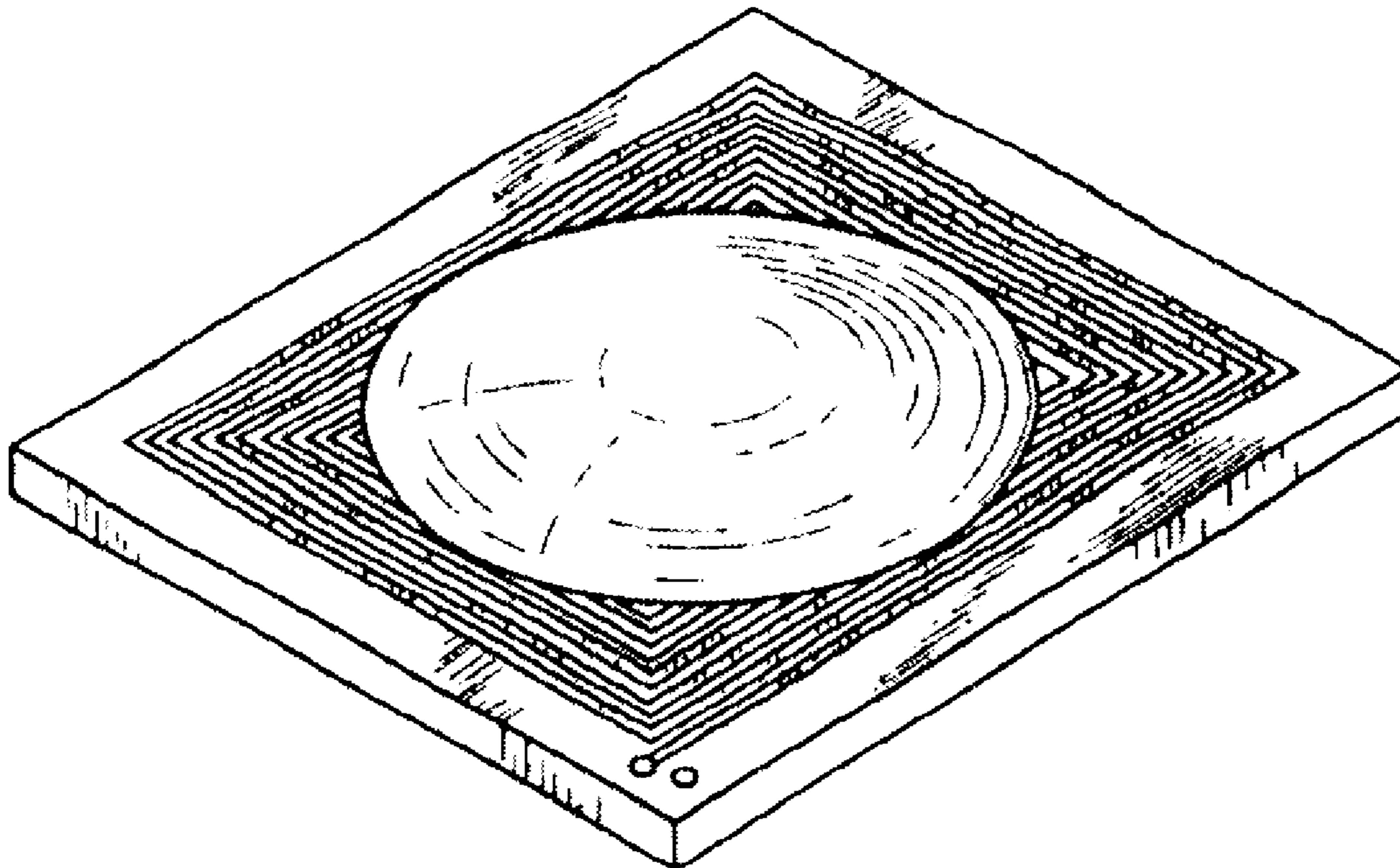
(57) **CLAIM**

The ornamental design for a semiconductor memory element, as shown and described.

DESCRIPTION

FIG. 1 is a top perspective view of a semiconductor memory element showing our new design; FIG. 2 is a side elevation view thereof, the opposite side view being a mirror image of that shown; FIG. 3 is a top plan view thereof; FIG. 4 is a bottom plan view thereof; and, FIG. 5 is a front elevation view thereof, the rear elevation view being a mirror image of that shown.

1 Claim, 2 Drawing Sheets



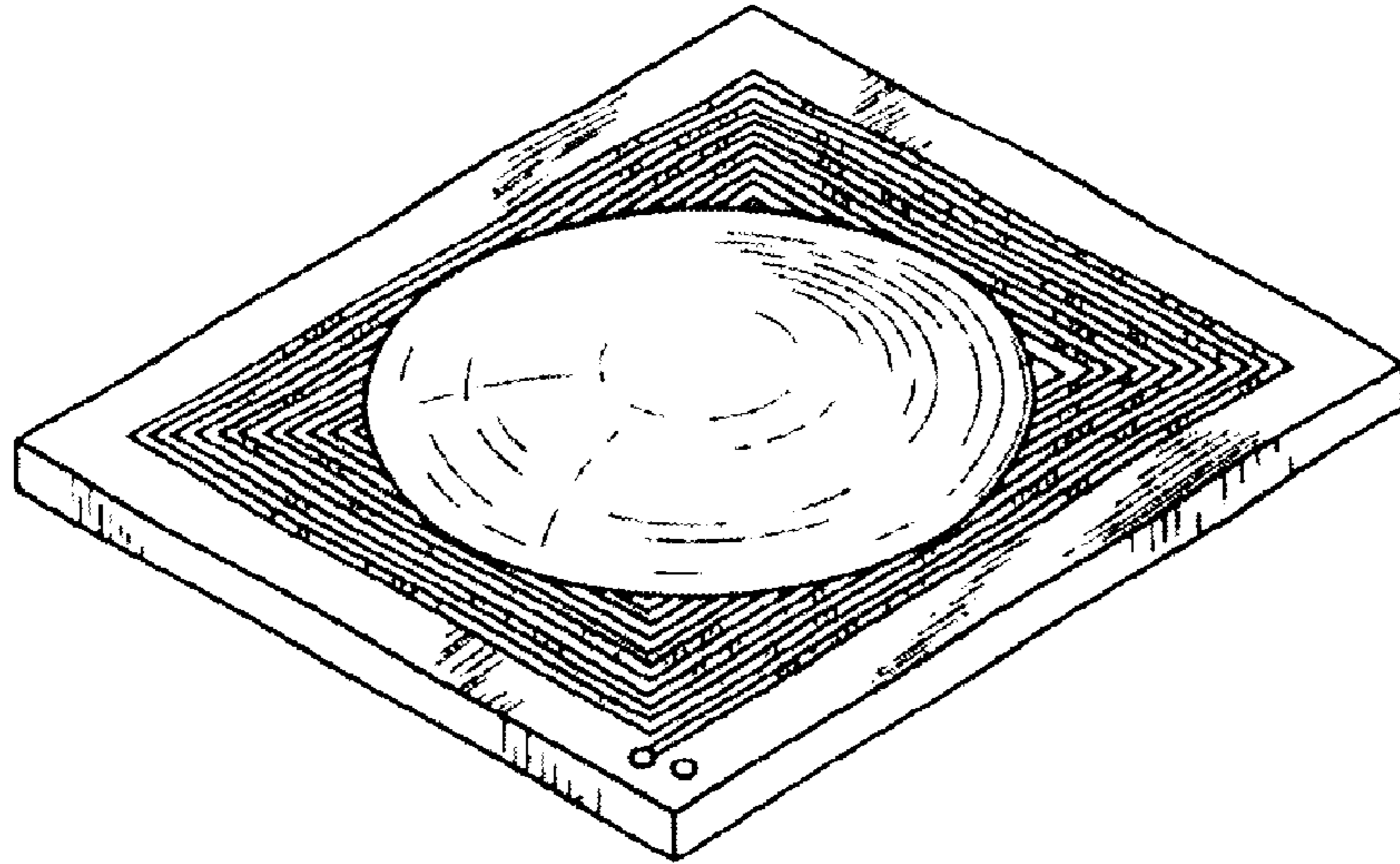


FIG. 1

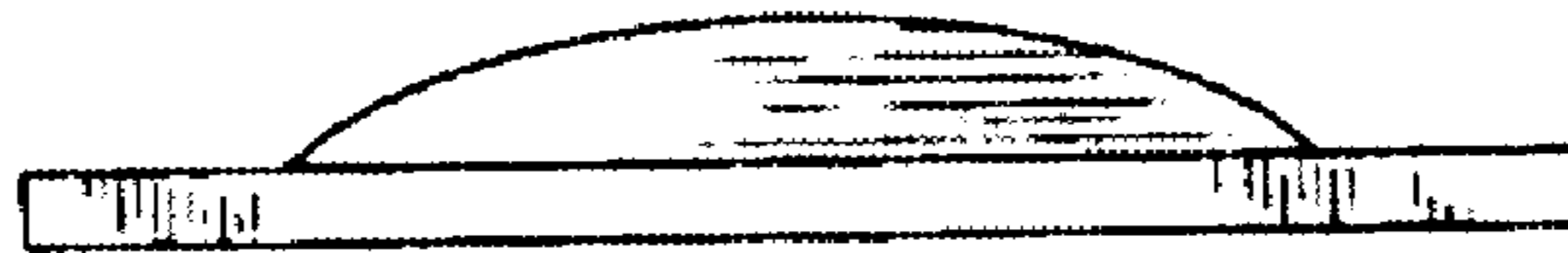


FIG. 2

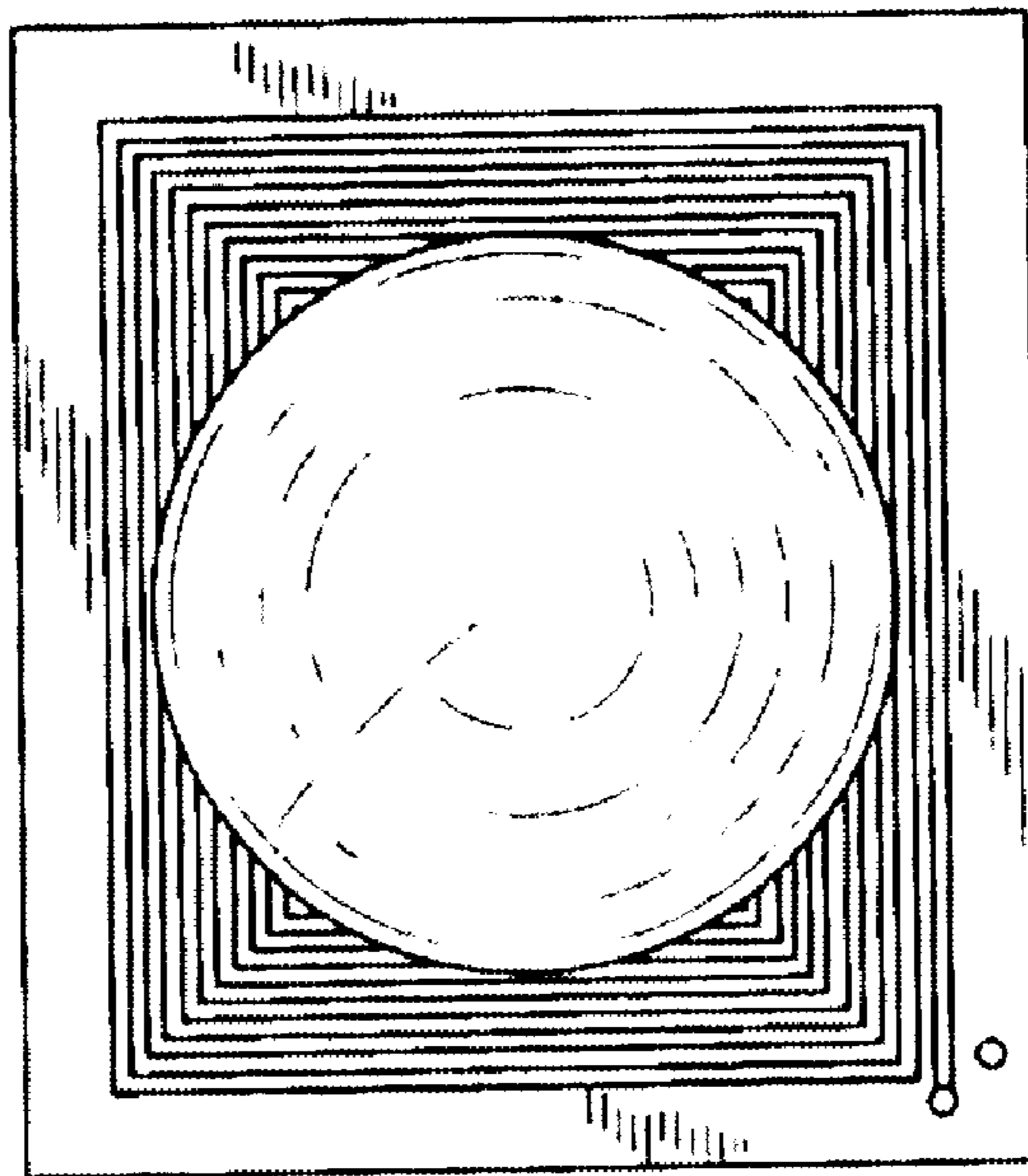


FIG. 3

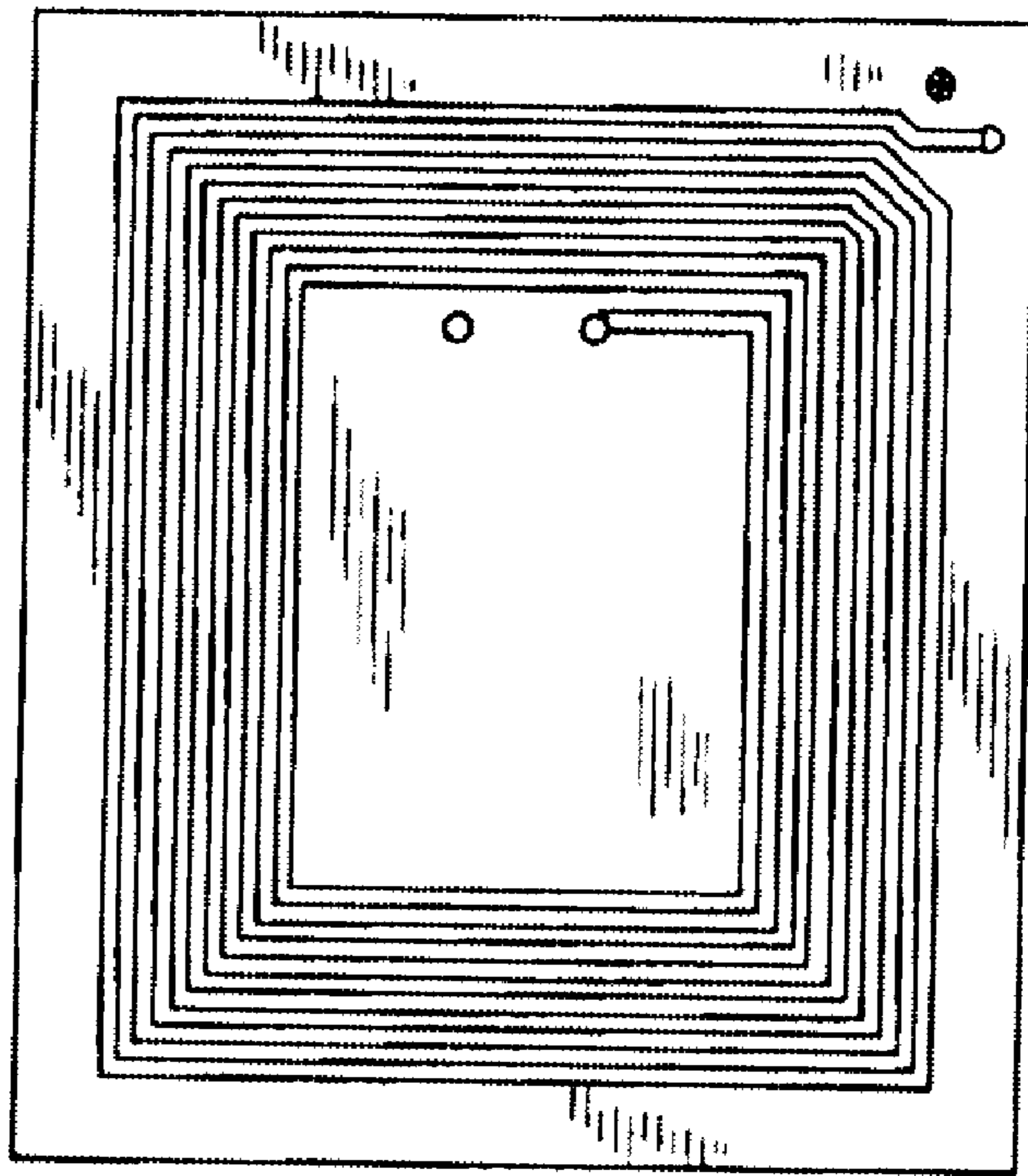


FIG. 4



FIG. 5